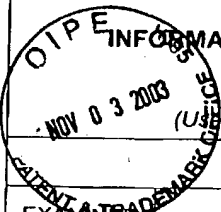


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Form PTO-1449 (MODIFIED)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. 039153-0447 (G1152)	SERIAL NO. 10/016,439
INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)		APPLICANT Lukanc et al.	
		FILING DATE 12/11/2001	GROUP ART UNIT 1756



U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE
NB	A1	6,410,193	06/25/2002	Stivers et al.	430	5	
	A2	6,057,063	05/02/2000	Liebmann et al.			
NB	A3	6,013,399	01/11/2000	Nguyen	430	5	
	A4	5,861,233	01/19/1999	Sekine et al.	430	296	
	A5	5,780,187	07/14/1998	Pierrat	430	5	
NB	A6	5,641,593	06/24/1997	Watanabe et al.	430	5	
	A7	5,619,059	04/08/1997	Li et al.	257	431	

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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION	
							YES	NO
NB	A10	EP 0 708 367 B1	01/14/1998	EPO			X	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

NB	A11	T. BRUNNER ET AL., "170 nm gates fabricated by phase-shift mask and top anti-reflector process," 182/SPIE Vol. 1927, Optical/Laser Microlithography VI, 1993, pps. 1-8.
NB	A12	KURT RONSE ET AL., "Comparison of various phase shift strategies and application to 0.35 μ m ASIC Designs," 2/SPIE Vol. 1927, Optical/Laser Microlithography VI, 1993, pps. 1-15.
NB	A13	J. M. CALVERT ET AL., "Projection X-Ray Lithography With Ultrathin Imaging Layers and Selective Electroless Metallization," Optical Engineering Vol. 32 No. 10, Oct. 1993., pp. 2437-2445
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EXAMINER <i>Richard B...</i>	DATE CONSIDERED 2/18/04
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* EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include any copy of this form with next communication to applicant.

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Form PTO-1449 (MODIFIED)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. 039153-0447 (G1152)		SERIAL NO. 10/016,439	
<div style="position: relative; height: 100px;"> <div style="position: absolute; top: 0; left: 0; width: 100%; height: 100%; border: 1px solid black; border-radius: 50%; text-align: center; color: white; font-weight: bold; font-size: 1.2em;"> INFORMATION DISCLOSURE CITATION (Use several sheets if necessary) </div> </div>				APPLICANT Lukanc et al.			
				FILING DATE 12/11/2001		GROUP ART UNIT 1756	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE
ny	A8	5,521,031	05/28/1996	Tennant et al.	430	5	RECEIVED NOV 12 2003 TC 1700
ny	A9	5,328,784	07/12/1994	Fukuda	430	5	
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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION YES NO
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ny	A17	I. NISHIYAMA ET AL., "Photon Energy Dependence of Synchrotron Radiation Induced Growth Suppression and Initiation in Al Chemical Vapor Deposition II. Surface Analysis by Auger Electron Spectroscopy," Applied Surface Science, Vol. 103, 1996, pp. 299-306					
ny	A18	O. R. WOOD II ET AL., "Use of Attenuated Phase Masks in Extreme Ultraviolet Lithography," Journal of Vacuum Science and Technology B, Vol. 15, No. 6, Nov/Dec 1997, pp. 2448-2451					
ny	A19	R. ZANONI ET AL., "Synchrotron-Radiation-Stimulated Tungsten Deposition on Silicon from W(CO) ₆ ," Journal of Vacuum Science and Technology A, Vol. 9, No. 3, May/June 1991, pp. 931-934.					
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	A21	U.S. Application Serial No. 09/772,577, entitled "PHASE SHIFT MASK AND SYSTEM AND METHOD FOR MAKING THE SAME" by Lukanc.					
EXAMINER <i>Michael Bar...</i>				DATE CONSIDERED 2/18/04			
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